

Notice of References Cited	Application/Control No. 10/586,810		Applicant(s)/Patent Under Reexamination MEUNIER-BEILLARD ET AL.	
	Examiner JOHN DOYLE		Art Unit 2891	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,506,427	04-1996	Imai, Kiyotaka	257/197
*	B	US-2005/0181569	08-2005	Koshimizu et al.	438/312
*	C	US-2005/0079678	04-2005	Verma et al.	438/312
*	D	US-6,509,242	01-2003	Frei et al.	438/312
*	E	US-6,455,364	09-2002	Asai et al.	438/235
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	I					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Schiz et al., Leakage Current Mechanisms in SiGe HBTs Fabricated Using Selective and NonSelective Epitaxy, November 2001, IEEE Transactions on Electron Devices, Col. 48, No. 11, Pages 2492-2493
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.